



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

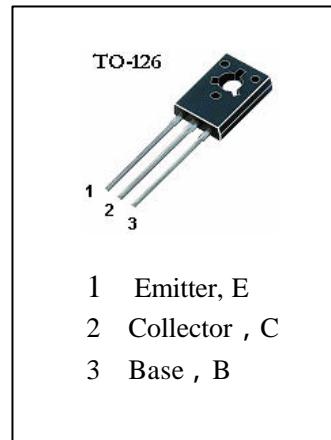
HSBD378

APPLICATIONS

Medium Power Linear switching Applications

ABSOLUTE MAXIMUM RATINGS (T_a=25)

T _{stg}	—Storage Temperature.....	-55~150
T _j	—Junction Temperature.....	150
P _c	—Collector Dissipation (T _c =25)	25W
V _{CBO}	—Collector-Base Voltage.....	-75V
V _{CEO}	—Collector-Emitter Voltage.....	-60V
V _{EBO}	—Emitter-Base Voltage.....	-5V
I _c	—Collector Current(Pulse).....	-3A
I _c	—Collector Current (DC)	-2A
I _b	—Base Current.....	-1A



ELECTRICAL CHARACTERISTICS (T_a=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I _{CBO}	Collector Cut-off Current			-2	μ A	V _{CB} =-60V, I _E =0
I _{EBO}	Emitter Cut-off Current			-100	μ A	V _{EB} =-5V, I _C =0
*H _{FE} (1)	DC Current Gain	40		375		V _{CE} =-2V, I _C =-150mA
*H _{FE} (2)	DC Current Gain	20				V _{CE} =-2V, I _C =-1A
*V _{CESAT}	Collector- Emitter Saturation Voltage			-1	V	I _C =-1A, I _B =-0.1A
*V _{BE(on)}	Base-Emitter On Voltage			-1.5	V	V _{CE} =-2V, I _C =-1A
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	-60			V	I _C =-100mA, I _B =0
BV _{CBO}	Collector-Base Breakdown Voltage	-75			V	I _C =-100 μ A, I _E =0
t _{ON}	Turn-On Time		50		nS	V _{CC} =-30V, I _C =-0.5A
t _{OFF}	Turn-Off Time		500		nS	

* Pulse Test: PW=350 μ S, Duty Cycle=2% Pulsed

h_{FE(3)} Classification

Classification	6	10	16	25
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h _{FE(3)}	40~100	63~160	100~250	150~375
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